11: (1) ("6723604").PN. 12: (1) ("6670241").PN. 13: (1) "6218245".PN. 14: (214407) dielectric 15: (904) 4 and (charge adj trapping) 16: (103) 5 and wordline\$1 17: (3) 6 and (deuterium or deuterated) 18: (1753) deuterium or deuterated 19: (1600) 8 and memory 10: (343) 9 and (duelectric) 11: (125) 10 and (deuterium or deuterated) 11: (125) 10 and (deuterium or deuterated) 11: (29) 13 and (deuterium or deuterated).cl 11: (29) 13 and (deuterium or deuterated).cl 11: (29) 13 and (low or (marge adj trapping) 11: (12) 13 and (low or (marge adj trapping) 11: (14) 15 and flash 11: (15 and flash) 11: (14) 15 and flash 11: (14) 14 and (diffus\$3 near9 (deuterium or alled).cl 11: (15 and flash) 11: (14) 14 and (diffus\$3 near9 (deuterium or alled).cl 11: (15 and flash) 11: (2002004716) 11: (2002004716)	emory 257/390 cate in evice 257/410 te	adj trapping ad	risval invent Hazama, Hir	
12: (1) ("6670241").PN: 13: (1) "6218245".PN. 14: (214407) dielectric 15: (904) 4 and (charge adj trapping) 16: (103) 5 and wordline\$1 17: (3) 6 and (deuterium or deuterated) 18: (11753) deuterium or deuterated 19: (1600) % and memory 10: (343) 9 and (dielectric) 11: (125) 10 and (deuterium or deuterated) 11: (125) 10 and (deuterium or deuterated) w 11: (125) 10 and (deuterium or deuterated) w 11: (29) 13 and (deuterium or deuterated).cl 11: (29) 13 and (Geuterium or deuterated).cl 11: (29) 13 and (Geuterium or deuterated).cl 11: (15 and flash 11: (14 and (diffus\$3 near9 (deuterium or ailed 11: (14) 15 and flash 11: (14) 14 and (diffus\$3 near9 (deuterium or ailed 11: (12) 12 11: (12) 202040140510 11: (14) 15 12: (15) 10 12: (14) 15 12: (15) 10 12: (15) 10	A (ONO ot (charge A Anno ot (ch	Max J R Current ZB Ret 257/261: 257/324: 257/221.19	risval invent Hazama, Hir	02 8 5 20 3 1
U I FT F Document 1D Issue Dat Fages Title C	Current 9 emory 257/390 cate in evice .257/410 te	R Current XR Ret 257/261: 257/324: 257/221.19	Hazama, Hir	
20040140510 device baving a C C C Semiconductor d and S01 substra and S01 substra Freess for red C C C Semiconductor d and S01 substra Freess for red Freess for red F C C Semiconductor d F F C C F F C C F C C Semiconductor d	oate in evice .257/410 te	257/3240 257/E21.19		oaki Rrrrrr
с. Г. Г. 20020047169 г. Г. Г. US 6740605 20040525 15 Process for red hydrogen contam п. Г. Г. US 6677213 20040113 11 SONOS structure .El	ucing 438/795		Kunikiyo, T	atsuya goccc
EI Hvdrogen contam E R T C US 6677213 20040113 11 SONOS structure EI including a deu		438/471;	Shiraiwa, H	idehiko s r r r r
	438/308 terated	438/473; 438/795	et al. Ramkumar, Krishnaswam Kamal, Tazr	v.et.al R C C C C
C C D D C 05 5670241 20051250 9 Semiconductor m	materia evice 257/411	257/347; 257/510;	al. Kunikiyo, T	
	12			
Chrone Marten			I	

· .

.

•